# 2SA2118

## Silicon PNP epitaxial planar type

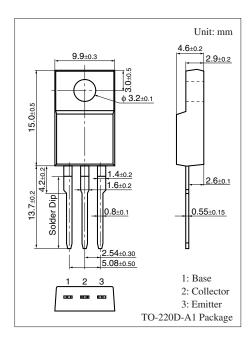
For power amplification
For TV vertical deflection output

#### ■ Features

- Satisfactory linearity of forward current transfer ratio h<sub>FE</sub>
- Dielectric breakdown voltage of the package: 5 kV
- Full-pack package which can be installed to the heat sink with one screw.

### ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-200	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-180	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	-6	V	
Collector current	$I_{C}$	-2	A	
Peak collector current	I <sub>CP</sub>	-3	A	
Collector power	P <sub>C</sub>	25	W	
dissipation $T_a = 25$ °C		2.0		
Junction temperature	$T_{j}$	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	



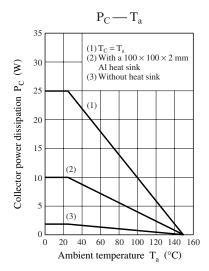
### ■ Electrical Characteristics $T_C = 25$ °C $\pm 3$ °C

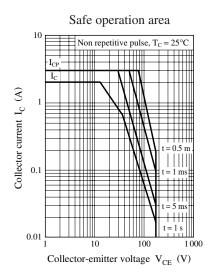
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_C = -50 \ \mu A, I_E = 0$	-200			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -5 \text{ mA}, I_{\rm B} = 0$	-180			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = -500 \ \mu A, I_C = 0$	-6			V
Base-emitter voltage	$V_{BE}$	$V_{CE} = -10 \text{ V}, I_{C} = -400 \text{ mA}$			-1	V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -200 \text{ V}, I_E = 0$			-50	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = -4 \text{ V}, I_C = 0$			-50	μΑ
Forward current transfer ratio	h <sub>FE1</sub> *	$V_{CE} = -10 \text{ V}, I_{C} = -150 \text{ mA}$	60		240	_
	h <sub>FE2</sub>	$V_{CE} = -10 \text{ V}, I_{C} = -400 \text{ mA}$	50			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$			-1	V
Transition frequency	$f_T$	$V_{CE} = -10 \text{ V}, I_{C} = -0.5 \text{ A}, f = 10 \text{ MHz}$		30		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

#### 2. \*: Rank classification

Rank	Q	Р
$h_{\rm FE1}$	60 to 140	100 to 240





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